

97-0252

The invention relates to the radio electric engineering and can be used for fabrication of photodetectors and optoelectronic devices on base thereof.

Summary of the invention consists in the fact that in the process for obtaining thin-film heterostructures on base of the A^2B^6 compound including vacuum deposition of layers in the presence of a temperature gradient between the evaporator and substrate, firstly, it is deposited a narrow-band component layer, it is sensitized with saturated aqueous cadmium chloride solution, it is fired and etched, then it is deposited a wide-band component layer.

The technical result consists in increasing the amount of charge carriers at the expense of the narrow-band component layer alloying.

Claims: 1

Fig.: 2